AP25P06S

-60V P-Channel Enhancement Mode MOSFET

Description

The AP25P06S uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 6V. This device is suitable for use as a Battery protection or in other Switching application.

General Features

V_{DS} = -60V I_D =-25A

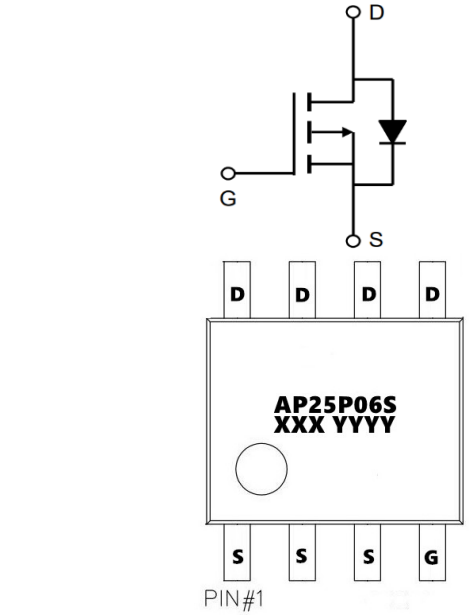
$R_{DS(ON)}$ < -13mΩ @ V_{GS}=-10V **(Type：10mΩ)**

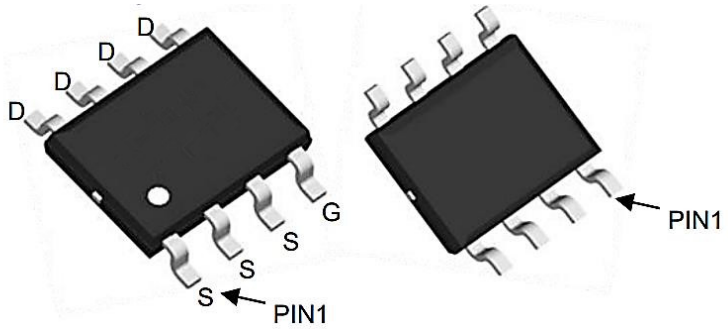
Application

Battery protection

Load switch

Uninterruptible power supply





Package Marking and Ordering Information

Product ID	Pack	Marking	Qty(PCS)
AP25P06S	SOP-8L	AP25P06S XXX YYYY	5000

Absolute Maximum Ratings (T_C=25℃unless otherwise noted)

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	-60	V
V_{GS}	Gate-Source Voltage	±20	V
I_D@T_C=25℃	Continuous Drain Current, -V_{GS} @ -10V[1]	-25	A
I_D@T_C=100℃	Continuous Drain Current, -V_{GS} @ -10V[1]	-15	A
I_{DM}	Pulsed Drain Current[2]	-75	A
EAS	Single Pulse Avalanche Energy[3]	450	mJ
P_D@T_C=25℃	Total Power Dissipation[4]	110	W
T_{STG}	Storage Temperature Range	-55 to 150	℃
T_J	Operating Junction Temperature Range	-55 to 150	℃
$R_{\theta JA}$	Thermal Resistance Junction-Ambient [1]	1.1	℃/W
$R_{\theta JC}$	Thermal Resistance Junction-Case[1]	85	℃/W

Electrical Characteristics (T_C=25℃unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BVDSS	Drain-Source Breakdown Voltage	V_{GS}=0V , I_D=-250uA	-60	-68	---	V
△BVDSS/△TJ	BV_{DSS} Temperature Coefficient	Reference to 25℃ , I_D=-1mA	---	-0.035	---	V/℃
RDS(ON)	Static Drain-Source On-Resistance[2]	V_{GS}=-10V , I_D=-20A	---	10	13	mΩ
		V_{GS}=-4.5V , I_D=-15A	---	13	18	
VGS(th)	Gate Threshold Voltage	V_{GS}=V_{DS} , I_D =-250uA	-1.0	-1.8	-2.5	V
△$V_{GS(th)}$	$V_{GS(th)}$ Temperature Coefficient		---	4.28	---	mV/℃
IDSS	Drain-Source Leakage Current	V_{DS}=-60V , V_{GS}=0V , T_J=25℃	---	---	1	uA
		V_{DS}=-60V , V_{GS}=0V , T_J=55℃	---	---	5	
IGSS	Gate-Source Leakage Current	V_{GS}=±20V , V_{DS}=0V	---	---	±100	nA
gfs	Forward Transconductance	V_{DS}=-5V , I_D=-20A	---	50	---	S
R_g	Gate Resistance	V_{DS}=0V , V_{GS}=0V , f=1MHz	---	2.0	---	Ω
Q_g	Total Gate Charge (-4.5V)	V_{DS}=-30V , V_{GS}=-10V , I_D=-20A	---	56	---	nC
Q_{gs}	Gate-Source Charge		---	11	---	
Q_{gd}	Gate-Drain Charge		---	9	---	
Td(on)	Turn-On Delay Time	V_{DD}=-30V , V_{GS}=-10V , R_G=3Ω, I_D=-20A	---	4.5	---	ns
T_r	Rise Time		---	2.5	---	
Td(off)	Turn-Off Delay Time		---	14.5	---	
T_f	Fall Time		---	3.8	---	
C_{iss}	Input Capacitance	V_{DS}=-15V , V_{GS}=0V , f=1MHz	---	3500	---	pF
Coss	Output Capacitance		---	600	---	
Crss	Reverse Transfer Capacitance		---	25	---	
I_S	Continuous Source Current[1,5]	V_G=V_D=0V , Force Current	---	---	-80	A
ISM	Pulsed Source Current[2,5]		---	---	-240	A
VSD	Diode Forward Voltage[2]	V_{GS}=0V , I_S=-1A , T_J=25℃	---	---	-1.2	V

Note :

1、The data tested by surface mounted on a 1 inch 2 FR-4 board with 2OZ copper.

2、The data tested by pulsed , pulse width ≦ 300us , duty cycle ≦ 2%

3、The EAS data shows Max. rating . The test condition is VDD =-48V,VGS =-10V,L=0.1mH,IAS =-41A

4、The power dissipation is limited by 150℃ junction temperature

5、The data is theoretically the same as I D and I DM , in real applications , should be limited by total power dissipation.

Typical Characteristics

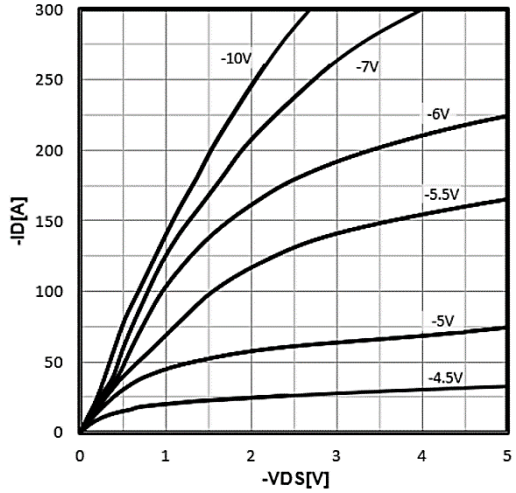


Figure 1. Type. Output Characteristics (Tj=25 ℃)

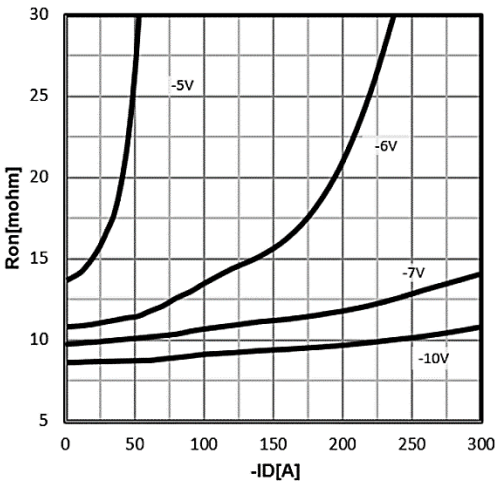


Figure 2. Type. drain-source on resistance

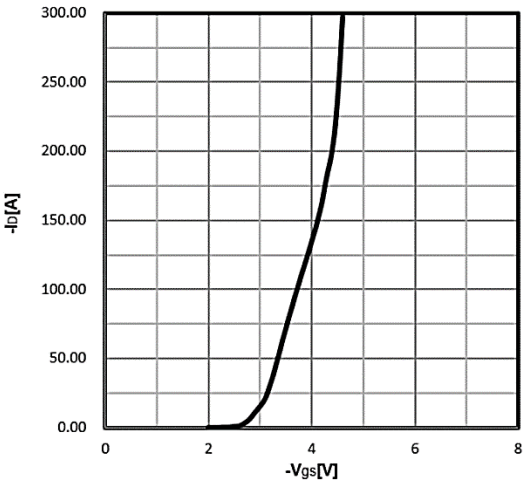


Figure 3. Type. transfer characteristics

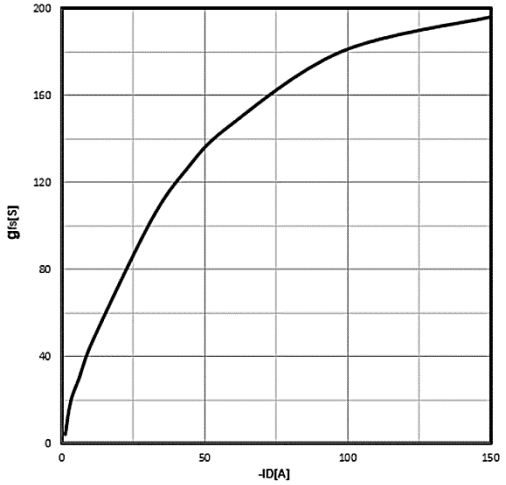


Figure 4. Type. forward transconductance

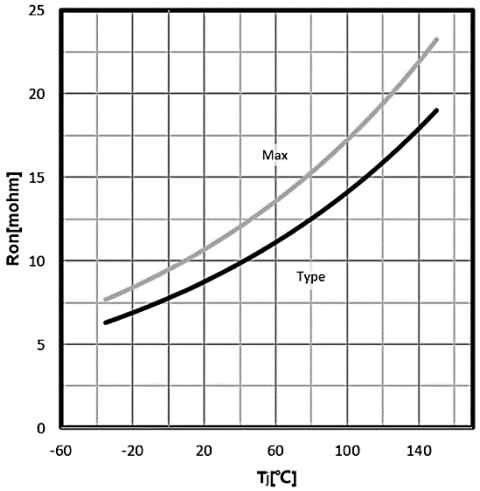


Figure 5. Drain-source on-state resistance
RDS(on) =f(Tj); ID =80A; VGS =10V

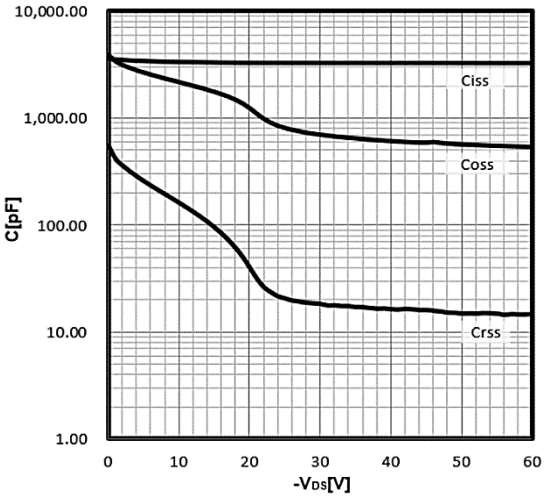


Figure 6 . Body-Diode Characteristics
C=f(VDS); VGS =0V; f=1MHz

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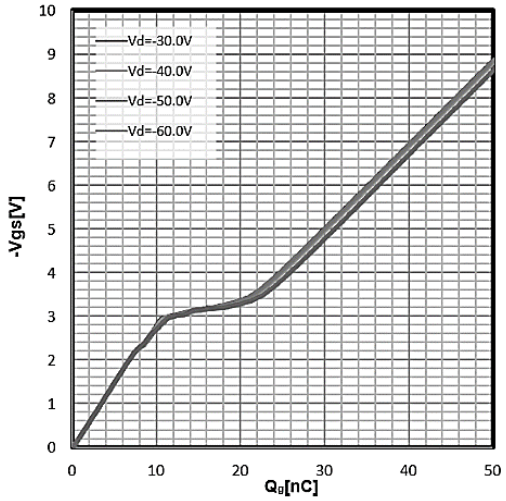


Figure 7. Typ. gate charge
VGS =f(Q gate) ; ID =20A

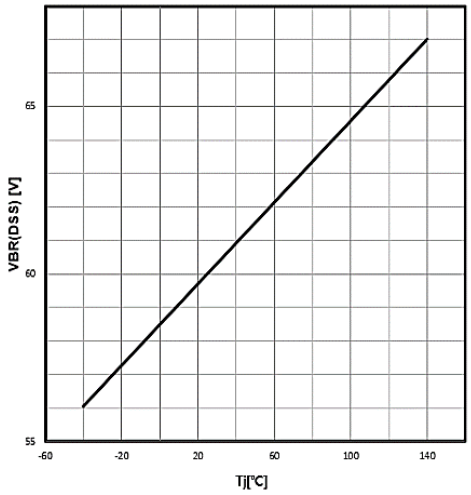


Figure 8. Drain Current Derating
VBR(DSS) =f(T j); I D =250uA

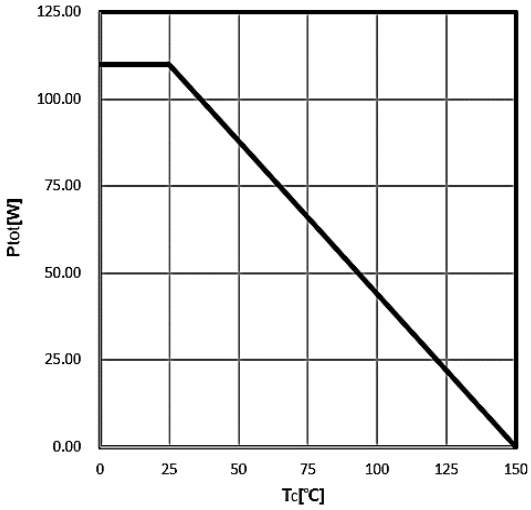


Figure 7. Power Dissipation

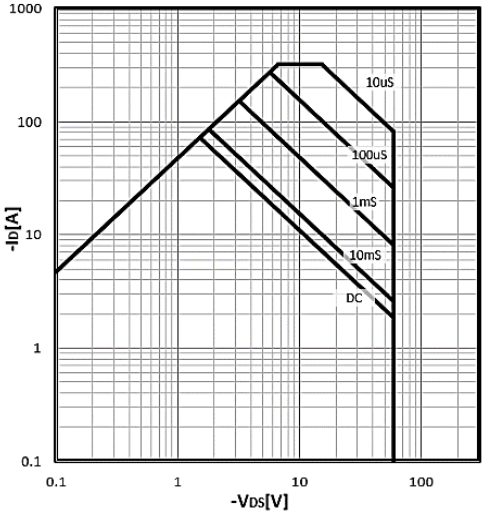


Figure 8. Safe operating area

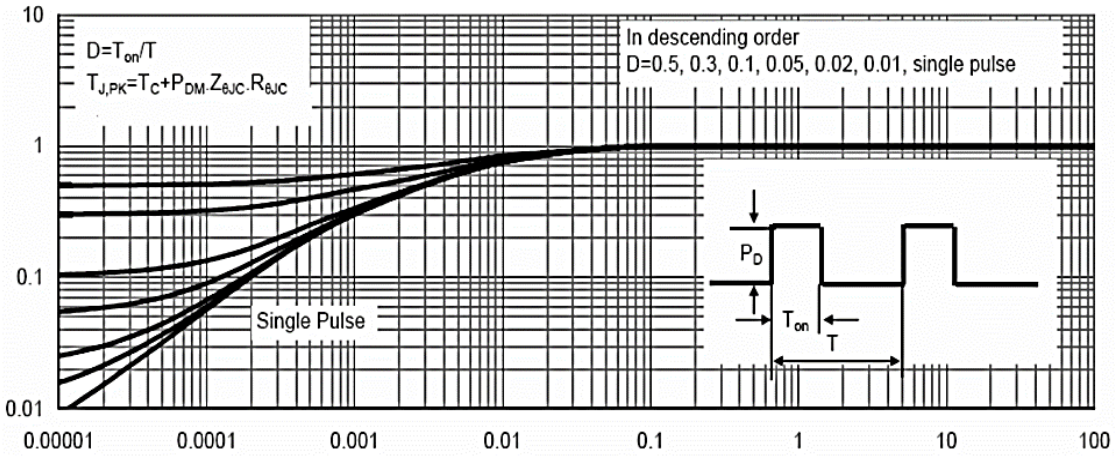
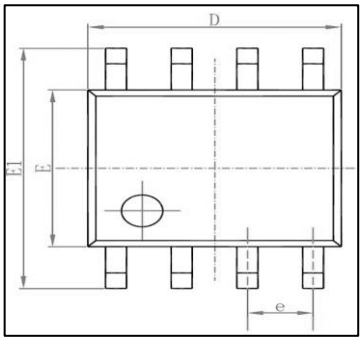
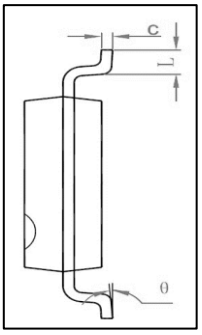


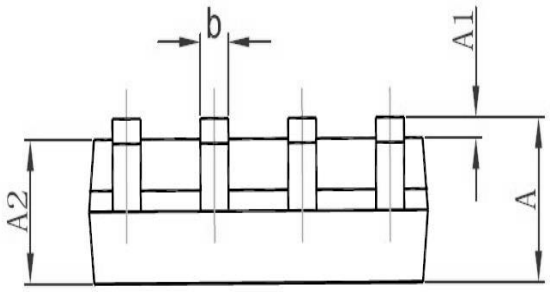
Figure 10. Max. transient thermal impedance

ZthJC =f(tp)

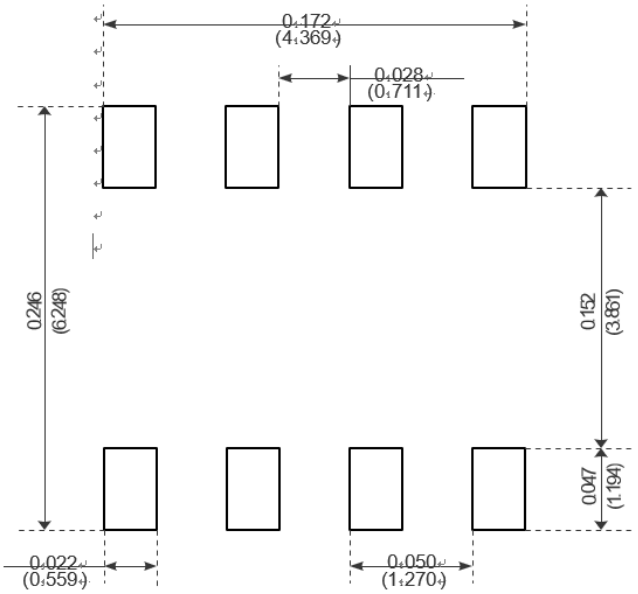
Package Mechanical Data-SOP-8







Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	1.350	1.750	0.053	0.069
A1	0.100	0.250	0.004	0.010
A2	1.350	1.550	0.053	0.061
b	0.330	0.510	0.013	0.020
c	0.170	0.250	0.006	0.010
D	4.700	5.100	0.185	0.200
E	3.800	4.000	0.150	0.157
E1	5.800	6.200	0.228	0.244
e	1.270 (BSC)		0.050 (BSC)	
L	0.400	1.270	0.016	0.050
θ	0°	8°	0°	8°



Recommended Minimum Pads